

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

**2SK2467-Y**

HIGH POWER AMPLIFIER APPLICATION

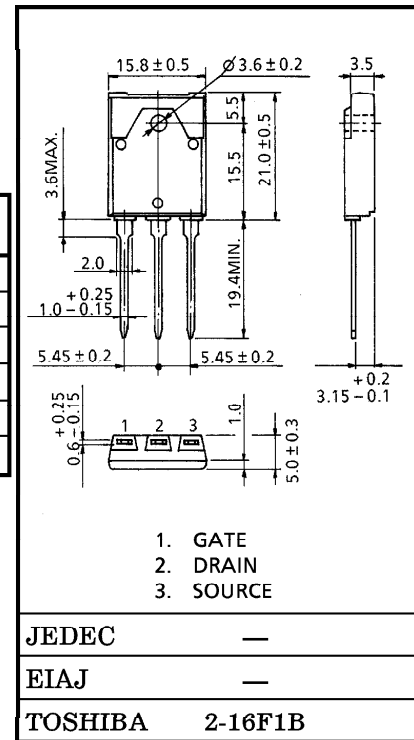
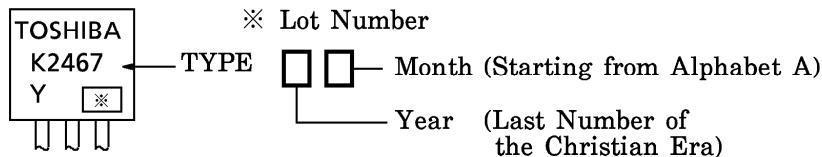
Unit in mm

- High Breakdown Voltage :  $V_{DSS}=180V$
- High Forward Transfer Admittance :  $|Y_{fs}|=4.0S$  (Typ.)

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

| CHARACTERISTIC                               | SYMBOL    | RATING         | UNIT       |
|----------------------------------------------|-----------|----------------|------------|
| Drain-Source Voltage                         | $V_{DSS}$ | 180            | V          |
| Gate-Source Voltage                          | $V_{GSS}$ | $\pm 20$       | V          |
| Drain Current                                | $I_D$     | 9              | A          |
| Drain Power Dissipation ( $T_c=25^\circ C$ ) | $P_D$     | 80             | W          |
| Channel Temperature                          | $T_{ch}$  | 150            | $^\circ C$ |
| Storage Temperature Range                    | $T_{stg}$ | $-55 \sim 150$ | $^\circ C$ |

## MARKING

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

Weight : 5.8g (Typ.)

| CHARACTERISTIC                     | SYMBOL         | TEST CONDITION                 | MIN. | TYP. | MAX.      | UNIT    |
|------------------------------------|----------------|--------------------------------|------|------|-----------|---------|
| Drain Cut-Off Current              | $I_{DSS}$      | $V_{DS}=180V, V_{GS}=0$        | —    | —    | 1.0       | mA      |
| Gate Leakage Current               | $I_{GSS}$      | $V_{DS}=0, V_{GS}=\pm 20V$     | —    | —    | $\pm 0.5$ | $\mu A$ |
| Drain-Source Breakdown Voltage     | $V_{(BR) DSS}$ | $I_D=10mA, V_{GS}=0$           | 180  | —    | —         | V       |
| Drain-Source Saturation Voltage    | $V_{DS(ON)}$   | $V_{GS}=10V, I_D=6A$           | —    | 2.5  | 5.0       | V       |
| Gate-Source Cut-off Voltage (Note) | $V_{GS(OFF)}$  | $V_{DS}=10V, I_D=0.1A$         | 1.4  | —    | 2.8       | V       |
| Forward Transfer Admittance        | $ Y_{fs} $     | $V_{DS}=10V, I_D=3A$           | —    | 4.0  | —         | S       |
| Input Capacitance                  | $C_{iss}$      | $V_{DS}=30V, V_{GS}=0, f=1MHz$ | —    | 700  | —         | pF      |
| Output Capacitance                 | $C_{oss}$      | $V_{DS}=30V, V_{GS}=0, f=1MHz$ | —    | 150  | —         | pF      |
| Reverse Capacitance                | $C_{rss}$      | $V_{DS}=30V, V_{GS}=0, f=1MHz$ | —    | 90   | —         | pF      |

(Note) :  $V_{GS(OFF)}$  Classification Y : 1.4~2.8

**This transistor is an electrostatic sensitive device.**  
**Please handle with caution.**

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